

In the Specification:

Please amend the paragraph beginning on page 7, line 30, as follows:

A1
Figs. 1 through 5 illustrate the sequence of processes for manufacturing a tantalum oxy nitride capacitor in accordance with the prior art as well as this disclosure, in which:

Please amend the paragraph beginning on page 8, line 23, as follows:

AR
Figs. 1 through 5 are views illustrating the disclosed sequence of processes for manufacturing a tantalum oxy nitride capacitor.

Please amend the paragraph beginning on page 8, line 26, as follows:

A3
In the process according to the disclosure, as illustrated in Fig. 1, a lower electrode 100 is formed on the surface of a semiconductor substrate 40 (not shown). At this time, the lower electrode is selected from undoped silicon, low doping silicon or doped/undoped silicon which are capable of MPS growth. At this time, a thin film used as the electrode is an amorphous silicon film deposited at a temperature of below about 560°C by using a gas containing a silicon source such as SiH₄, Si₂H₆, SiH₂Cl₂ and the like and a gas containing PH₃ such as PH₃/N₂, ~~PH₃/He~~ PH₃/H₂, PH₃/SiH₄, PH₃/Ar and the like. At this time, conditions such as an amount of gas, pressure, etc. can be made suitable for a selective polycrystalline silicon growing technique(MPS growing technique).